

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	94753	(ONO (oxide near5 nitride near5 oxide))	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/21 17:29
L2	30074	1 and gate	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/21 17:30
L3	10934	2 and spacer	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/21 17:31
L4	5621	3 and ((conduct\$3 silicon polysilicon poly?silicon (poly near3 crystalline near3 silicon)) near5 spacer)	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/21 15:33
L5	5574	4 and (etch\$3 pattern\$4)	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/21 15:33
L6	5219	5 and (dop\$3 implant\$3)	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/21 15:35
L7	5219	6 and (oxid\$6 thermal)	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/21 15:37
L8	1397	7 and float\$3	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/21 15:37
L9	86815	(ONO (oxide near5 nitride near5 oxide))	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/21 17:29
L10	5192	9 and gate	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/21 17:30
L11	662	10 and spacer	EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/21 17:31